

STRUCTURES AND METHODS FOR IMPROVED CAPACITOR CELLS IN INTEGRATED CIRCUITS

Abstract of the Disclosure

Systems, devices, structures, and methods are described that inhibit atomic migration that creates an open contact between a metallization layer and a conductive layer of a semiconductor structure. A layer of an inhibiting substance
5 may be used to inhibit a net flow of atoms so as to maintain conductivity between the metallization layer and the conductive layer of the semiconductor structure. Such layer of inhibiting substance acts even with the presence of point defects for a given temperature.

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